

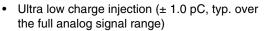
1.0 pC Charge Injection, 100 pA Leakage, 4-Channel Multiplexer

DESCRIPTION

The DG604 is an analog 4-channel CMOS, multiplexer, designed to operate from a + 2.7 V to + 12 V single supply or from $\pm 2.7 \text{ V}$ to $\pm 5.0 \text{ V}$, dual supplies. The DG604 is fully specified at + 3 V, + 5 V and $\pm 5 \text{ V}$. All control logic inputs have guaranteed 2 V logic high limits when operating from + 5 V or $\pm 5 \text{ V}$ supplies and 1.4 V when operating from a 3 V supply.

The DG604 switches conduct equally well in both directions and offer rail to rail analog signal handling. < 1 pC low charge injection, coupled with very low switch capacitance and leakage current makes this product ideal for use in precision instrumentation applications. Operating temperature range is specified from - 40 °C to + 125 °C. The DG604 is available in 14 lead TSSOP and the space saving 1.8 mm x 2.6 mm miniQFN package.

FEATURES





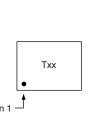
RoHS

- Leakage current < 0.5 nA max. at 85 °C (for DG604EQ-T1-E3)
- Low switch capacitance (C_{soff}, 3 pF typ.)
- Low R_{DS(on)} 115 Ω max.
- Fully specified with single supply operation at 3.0 V, 5.0 V and dual supplies at ± 5.0 V
- Low voltage, 2.5 V CMOS/TTL compatible
- 400 MHz. 3 dB bandwidth
- Excellent isolation and crosstalk performance (typ. > 60 dB at 10 MHz)
- Fully specified from 40 °C to 85 °C and 40 °C to + 125 °C
- 14 pin TSSOP and 16 pin miniQFN package (1.8 mm x 2.6 mm)

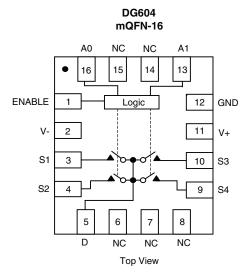
APPLICATIONS

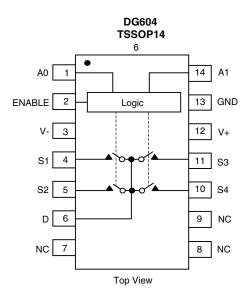
- · High-end data acquisition
- · Medical instruments
- Precision instruments
- High speed communications applications
- Automated test equipment
- Sample and hold applications

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: Txx for DG604 (miniQFN16) xx = Date/Lot Traceability Code





DG604

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TRUTH TABLE			
Enable	Select	ed Input	On Switches
Input	A1	A0	DG604
L	Х	X	All Switches Open
Н	L	L	D to S1
Н	L	Н	D to S2
Н	Н	L	D to S3
Н	Н	Н	D to S4

ORDERING INFORMA	ORDERING INFORMATION					
Temp. Range	Package	Part Number				
40 °C to 10E °C8	14 pin TSSOP	DG604EQ-T1-E3				
- 40 °C to 125 °C ^a	16 pin miniQFN	DG604EN-T1-E4				

Notes:

a. - 40 °C to 85 °C datasheet limits apply.

ABSOLUTE MAXIMUM RAT	FINGS T _A = 25 °C, unless of	therwise noted	
Parameter		Limit	Unit
V+ to V-		14	
GND to V-		7	\Box \lor
Digital Inputs ^a , V _S , V _D		(V-) - 0.3 to (V+) + 0.3 or 30 mA, whichever occurs first	
Continuous Current (Any Terminal)		30	m A
Peak Current, S or D (Pulsed 1 ms, 10 %	6 Duty Cycle)	100	mA
Storage Temperature		- 65 to 150	°C
Power Dissipation (Package) ^b	14 pin TSSOP ^c	450	mW
Power Dissipation (Package)	16 pin miniQFN ^{d, e}	525	IIIVV
Thermal Resistance (Package) ^b	14 pin TSSOP	178	C/W
memai nesisiance (Package)	16 pin miniQFN	152	7

Notes:

- a. Signals on SX, DX, or INX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 5.6 mW/°C above 70 °C.
- d. Derate 6.6 mW/°C above 70 °C.
- e. Manual soldering with iron is not recommended for leadless components. The miniQFN-16 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

SPECIFICATIONS	SPECIFICATIONS FOR DUAL SUPPLIES										
		Test Conditions			- 40 °C t	o 125 °C	- 40 °C				
Parameter	Symbol	Unless Otherwise Specified V+ = 5 V, V- = - 5 V V _{IN A0, A1 and ENABLE} = 2.0 V, 0.8 V ^a	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit		
Analog Switch	Analog Switch										
Analog Signal Range ^e	V _{ANALOG}		Full		- 5	5	- 5	5	V		
On-Resistance	R _{DS(on)}	$I_S = 1 \text{ mA}, V_D = -3 \text{ V}, 0 \text{ V}, +3 \text{ V}$	Room Full	70		115 160		115 140			
On-Resistance Match	ΔR _{ON}	$I_S = 1 \text{ mA}, V_D = \pm 3 \text{ V}$	Room Full	1		5 6.5		5 6.5	Ω		
On-Resistance Flatness	R _{FLATNESS}	I _S = 1 mA, V _D = -3 V, 0 V, +3 V	Room Full	10		20 33		20 22			





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		Test Conditions			40.00	o 125 °C	40.00	to 85 °C	l
		Unless Otherwise Specified			- 40 °C t	0 125 °C	- 40 °C	10 85 0	
Parameter	Symbol	V+ = 5 V, V- = -5 V $V_{\text{IN A0, A1 and ENABLE}} = 2.0 \text{ V}, 0.8 \text{ V}^{\text{a}}$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch	•	IIV AO, AT AND ENABLE		<u>,, </u>	l				l
Switch Off	I _{S(off)}	V. 55VV 55V	Room	± 0.01	- 0.1	0.1	- 0.1	0.1	
Leakage Current		$V_{+} = 5.5 \text{ V}, V_{-} = -5.5 \text{ V}$ $V_{D} = \pm 4.5 \text{ V}, V_{S} = \pm 4.5 \text{ V}$	Full Room	± 0.01	- 18 - 0.1	18 0.1	- 0.5 - 0.1	0.5	
(for 14 pin TSSOP)	I _{D(off)}	D , 3 +	Full	± 0.01	- 18	18	- 0.5	0.5	
Channel On Leakage Current	le c	V+ = 5.5 V, V- = - 5.5 V,	Room	± 0.01	- 0.1	0.1	- 0.1	0.1	
(for 14 pin TSSOP)	I _{D(on)}	$V_S = V_D = \pm 4.5 \text{ V}$	Full		- 18	18	- 0.5	0.5	^
Switch Off	I _{S(off)}	V. EEVV EEV	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1	nA
Leakage Current		$V_{+} = 5.5 \text{ V}, V_{-} = -5.5 \text{ V}$ $V_{D} = \pm 4.5 \text{ V}, V_{S} = \mp 4.5 \text{ V}$	Room	± 0.01	- 18	10	- 2 - 1	2	
(for 16 pin miniQFN)	I _{D(off)}	D - 7 3	Full	± 0.01	- 18	18	- 2	2	
Channel On	le c	V+ = 5.5 V, V- = - 5.5 V,	Room	± 0.01	- 1	1	- 1	1	
Leakage Current (for 16 pin miniQFN)	I _{D(on)}	$V_S = V_D = \pm 4.5 \text{ V}$	Full		- 18	18	- 2	2	
Digital Control									
Input Current, V _{IN} Low	I _{IL}	V _{IN A0, A1 and ENABLE} Under Test = 0.8 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	
Input Current, V _{IN} High	I _{IH}	V _{IN A0, A1 and ENABLE} Under Test = 2.0 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	μΑ
Input Capacitance ^e	C _{IN}	f = 1 MHz	Room	3.4					pF
Dynamic Characteristics									
Transition Time	t _{TRANS}	$V_{S(CLOSE)} = 3 \text{ V}, V_{S(OPEN)} = 0.0 \text{ V},$ $R_L = 300 \Omega, C_L = 35 \text{ pF}$	Room Full	20		70 105		70 80	
Turn-On Time	t _{ON}	$R_L = 300 \Omega, C_L = 35 pF$	Room Full	16		60 90		60 65	ns
Turn-Off Time	t _{OFF}	V _S = ± 3 V	Room Full	15		52 76		52 56	115
Break-Before-Make Time Delay	t_D	$V_S = 3 \text{ V}$ $R_L = 300 \Omega, C_L = 35 \text{ pF}$	Room Full	15	10		10		
Charge Injection ^e	Q	$V_g = 0 \text{ V, R}_g = 0 \Omega, C_L = 1 \text{ nF}$	Room	0.7					рC
Off Isolation ^e	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	Room	- 72					dB
Bandwidth ^e	BW	$R_L = 50 \Omega$	Room	400					MHz
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	Room	- 81					dB
Source Off Capacitance ^e	$C_{S(off)}$		Room	2.7					
Drain Off Capacitance ^e	$C_{D(off)}$	f = 1 MHz	Room	7.3					pF
Channel On Capacitance ^e	$C_{D(on)}$		Room	13.8					
Total Harmonic Distortion ^e	THD	Signal = 1 V_{RMS} , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	0.01					%
Power Supplies									
Power Supply Current	l+		Room Full	0.001		0.5 1		0.5 1	
		•			1 = =	. — —			I
Negative Supply Current	l-	V _{IN} = 0 V, or V+	Room Full	- 0.001	- 0.5 - 1		- 0.5 - 1 - 0.5		μΑ

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		Test Conditions			- 40 °C to 125 °C - 40 °C to 85 °C				
		Unless Otherwise Specified V+ = 5 V, V- = 0 V V _{IN A0, A1 and ENABLE} = 2.0 V, 0.8 V ^a	Temp.b						
Parameter	Symbol			Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Uni
Analog Switch									
Analog Signal Range ^e	V_{ANALOG}		Full			5		5	V
On-Resistance	R _{DS(on)}	$I_S = 1 \text{ mA}, V_D = +3.5 \text{ V}$	Room Full	120		170 250		170 200	Ω
On-Resistance Match	ΔR_{ON}	$I_S = 1 \text{ mA}, V_D = +3.5 \text{ V}$	Room Full	3		5 12		5 10	32
Switch Off Leakage Current	I _{S(off)}	V+ = 5.5 V, V- = 0 V	Room Full	± 0.01	- 0.1 - 18	0.1 18	- 0.1 - 0.5	0.1 0.5	
(for 14 pin TSSOP)	I _{D(off)}	$V_D = 1 \text{ V}/4.5 \text{ V}, V_S = 4.5 \text{ V}/1 \text{ V}$	Room Full	± 0.01	- 0.1 - 18	0.1 18	- 0.1 - 0.5	0.1 0.5	
Channel On Leakage Current (for 14 pin TSSOP)	$I_{D(on)}$	V+ = 5.5 V, V- = 0 V $V_S = V_D = 1 \text{ V}/4.5 \text{ V}$	Room Full	± 0.01	- 0.1 - 18	0.1 18	- 0.1 - 0.5	0.1 0.5	
Switch Off Leakage Current	I _{S(off)}	V+ = 5.5 V, V- = - 5.5 V	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	nA
(for 16 pin miniQFN)	I _{D(off)}	$V_D = 1 \text{ V}/4.5 \text{ V}, V_S = 4.5 \text{ V}/1 \text{ V}$	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	
Channel On Leakage Current (for 16 pin miniQFN)	$I_{D(on)}$	V+ = 5.5 V, V- = 0 V, $V_S = V_D = 1 \text{ V}/4.5 \text{ V}$	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	
Digital Control									
Input Current, V _{IN} Low	ΙL	V _{IN A0, A1 and ENABLE} Under Test = 0.8 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	
Input Current, V _{IN} High	I _H	V _{IN A0, A1 and ENABLE} Under Test = 2.0 V	Full	0.005	- 0.1	0.1	- 0.1	0.1	μΑ
Input Capacitance	C _{IN}	f = 1 MHz	Room	4.3					рF
Dynamic Characteristics									
Transition Time	t _{TRANS}		Room Full	36		75 120		75 95	
Enable Turn-On Time	t _{ON(EN)}	$V_{S(CLOSE)} = 3 \text{ V}, V_{S(OPEN)} = 0.0 \text{ V},$ $R_L = 300 \Omega, C_L = 35 \text{ pF}$	Room Full	30		70 102		70 80	- ns
Enable Turn-Off Time	t _{OFF(EN)}		Room Full	17		47 88		47 63	
Break-Before-Make-Time	t _{BMM}		Room Full	23	5		5		
Charge Injection	Q	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega, V_{GEN} = 0 V$	Full	0.15					рС
Off-Isolation ^e	OIRR	$f = 10 \text{ MHz}, R_L = 50 \Omega, C_L = 5 \text{ pF}$	Room	- 58				<u> </u>	dB
Crosstalk ^e	X _{TALK}		Room	- 81					u.b
Bandwidth ^e	BW	$R_L = 50 \Omega$	Room	330					MH:
Total Harmonic Distortion	THD	Signal = 1 V_{RMS} , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	0.009					%
Source Off Capacitance ^e	C _{S(off)}			3.1					
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room	11.6					рF
Channel On Capacitance ^e	C _{D(on)}			16.2					1
Power Supplies		<u> </u>							
Power Supply Current	l+		Room Full	0.001		0.5 1		0.5 1	
Negative Supply Current	I-	V _{IN} = 0 V, or V+	Room Full	- 0.001	- 0.5 - 1		- 0.5 - 1		μΑ
Ground Current	I _{GND}		Room Full	- 0.001	- 0.5 - 1		- 0.5 - 1		



		Test Conditions Unless Otherwise Specified V+ = 3 V, V- = 0 V			- 40 °C to + 125 °C		- 40 °C to + 85 °C		
Parameter	Symbol		Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full			3		3	V
On-Resistance	R _{DS(ON)}	$I_S = 1 \text{ mA}, V_D = + 1.5 \text{ V}$	Room Full	200		245 325		245 290	Ω
On-Resistance Match	ΔR _{ON}	$I_S = 1 \text{ mA}, V_D = + 1.5 \text{ V}$	Room Full	5		6 13		11 6	22
Switch Off Leakage Current	I _{S(off)}	V+ = 3 V, V- = 0 V	Room Full	± 0.01	- 0.1 - 18	0.1 18	- 0.1 - 0.5	0.1 0.5	
(for 14 pin TSSOP)	I _{D(off)}	$V_D = 1 \text{ V/3 V}, V_S = 3.0 \text{ V/1 V}$	Room Full	± 0.01	- 0.1 - 18	0.1 18	- 0.1 - 0.5	0.1 0.5	
Channel On Leakage Current (for 14 pin TSSOP)	I _{D(on)}	V+ = 3 V, V- = 0 V $V_S = V_D = 1 V/3.0 V$	Room Full	± 0.01	- 0.1 - 18	0.1 18	- 0.1 - 0.5	0.1 0.5	
Switch Off Leakage Current	I _{S(off)}	V+ = 3.3 V, V- = 0 V	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	nA
(for 16 pin miniQFN)	I _{D(off)}	$V_D = 1 \text{ V/3 V}, V_S = 3 \text{ V/1 V}$	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	
Channel On Leakage Current (for 16 pin miniQFN)	I _{D(on)}	V+ = 3.3 V, V- = 0 V V _D = 1 V/3 V, V _S = 3 V/1 V	Room Full	± 0.01	- 1 - 18	1 18	- 1 - 2	1 2	
Digital Control	<u>'</u>		I.	•		•			
Input Current, V _{IN} Low	ΙL	V _{IN A0, A1 and ENABLE} Under Test = 0.6 V	Full	0.005	- 1	1	- 1	1	4
Input Current, V _{IN} High	I _H	V _{IN A0, A1 and ENABLE} Under Test = 1.4 V	Full	0.005	- 1	1	- 1	1	μΑ
Input Capacitance	C _{IN}	f = 1 MHz	Room	4.3					pF
Dynamic Characteristics									
Transition Time	t _{TRANS}		Room Full	95		130 190		130 160	
Enable Turn-On Time	t _{ON(EN)}	$V_{S(CLOSE)} = 3.0 \text{ V}, V_{S(OPEN)} = 0.0$ V, R _L = 300 \Omega, C _L = 35 pF	Room Full	77		108 161		108 131	ns
Enable Turn-Off Time	t _{OFF(EN)}		Room Full	35		76 112		76 88	
Break-Before-Make-Time	t _{BMM}		Room Full	45	5		5		
Charge Injection	Q	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega, V_{GEN} = 0 V$	_	0.1					рС
Off-Isolation ^e	OIRR	$f = 10 \text{ MHz}, R_L = 50 \Omega, C_L = 5 \text{ pF}$	Room	- 58					dB
Crosstalke	X _{TALK}	B 50.0	Room	- 90					
Bandwidthe	BW	$R_L = 50 \Omega$	Room	290					MH:
Total Harmonic Distortion	THD	Signal = 1 V_{RMS} , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	0.09					%
Source Off Capacitance ^e	C _{S(off)}			3.1					
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room	11.7					pF
Channel On Capacitance ^e	C _{D(on)}			16.5					
Power Supplies									
Power Supply Current	l+		Room Full	0.001		0.5 1		0.5 1	
Negative Supply Current	l-	V _{IN} = 0 V, or V+	Room Full	- 0.001	- 0.5 - 1		- 0.5 - 1		μΑ
Ground Current	I _{GND}		Room Full	- 0.001	- 0.5 - 1		- 0.5 - 1		
		-							

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

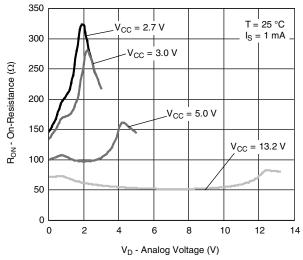
Document Number: 69934 S09-0280-Rev. B, 16-Feb-09

DG604

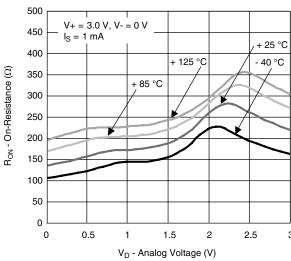
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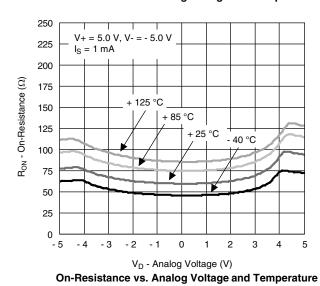
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. V_D (Single Supply Voltage)

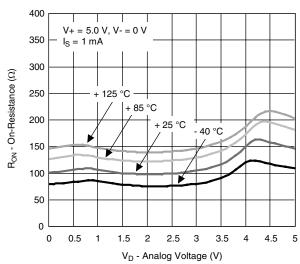


On-Resistance vs. Analog Voltage and Temperature

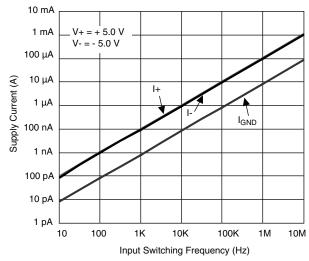


160 140 = - 2.7 V V + = +6.2 V120 = - 6.2 V V + = +5.0 VR_{ON} - On-Resistance (Ω) = - 5.0 V 100 80 60 40 T = 25 °C 20 $I_S = 1 \text{ mA}$ 0 - 8 - 6 - 2 6 V_D - Analog Voltage (V)

On-Resistance vs. V_D (Dual Supply Voltage)



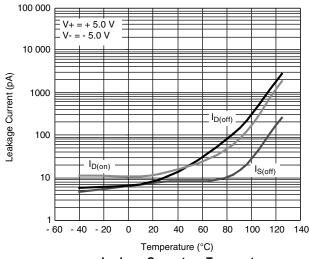
On-Resistance vs. Analog Voltage and Temperature



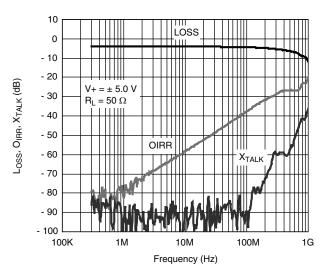
Supply Current vs. Input Switching Frequency



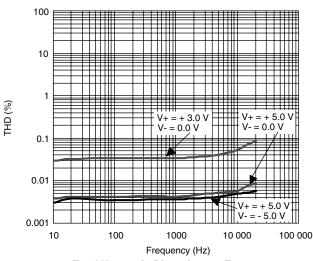
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



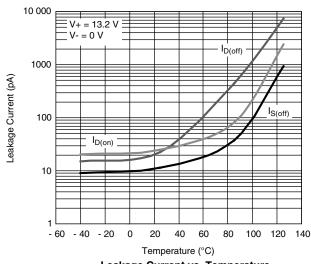
Leakage Current vs. Temperature



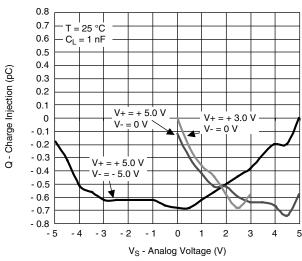
Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



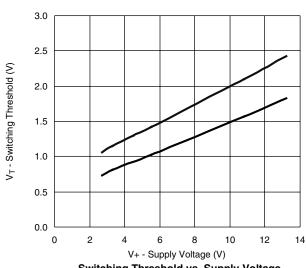
Total Harmonic Distortion vs. Frequency



Leakage Current vs. Temperature



Charge Injection vs. Analog Voltage



Switching Threshold vs. Supply Voltage

Document Number: 69934 S09-0280-Rev. B, 16-Feb-09

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TEST CIRCUITS

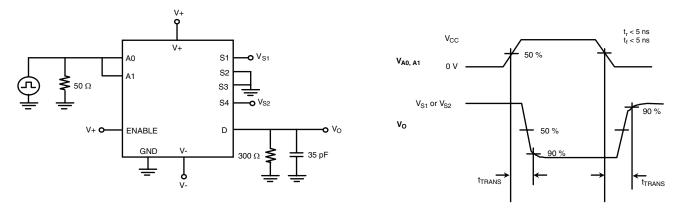


Figure 1. Transition Time

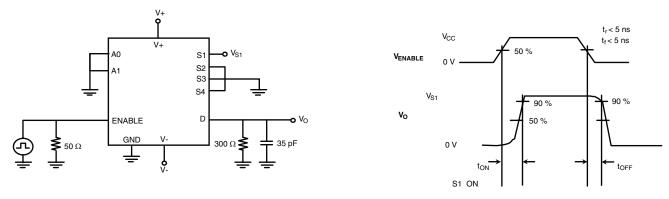


Figure 2. Enable Switching Time

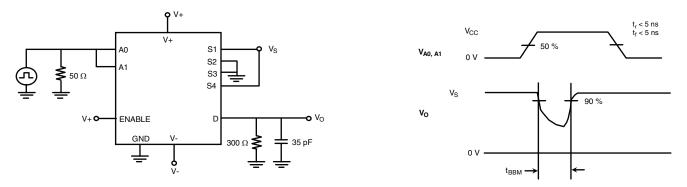


Figure 3. Break-Before-Make

TEST CIRCUITS

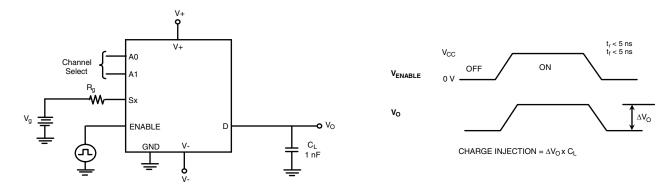


Figure 4. Charge Injection

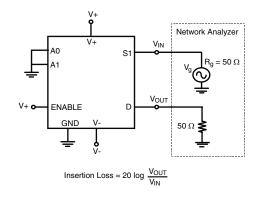


Figure 5. Insertion Loss

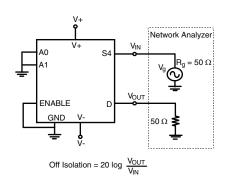


Figure 6. Off-Isolation

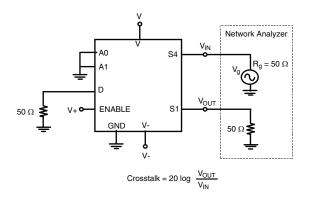


Figure 7. Crosstalk

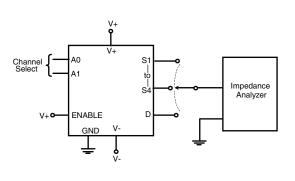


Figure 8. Source/Drain Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg269934.

Document Number: 69934 S09-0280-Rev. B, 16-Feb-09

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